

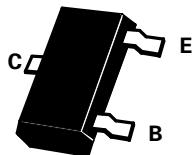
SOT23 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

ISSUE 3 - NOVEMBER 1995



FMMT596

PARTMARKING DETAIL – 596



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-220	V
Collector-Emitter Voltage	V_{CEO}	-200	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-0.3	A
Base Current	I_B	-200	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	500	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-220		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-200		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		-100	nA	$V_{CB} = -200\text{V}$
Emitter Cut-Off Current	I_{EBO}		-100	nA	$V_{EB} = -4\text{V}$
Collector-Emitter Cut-Off Current	I_{CES}		-100	nA	$V_{CES} = -200\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.2 -0.35	V	$I_C = -100\text{mA}, I_B = -10\text{mA}$ $I_C = -250\text{mA}, I_B = -25\text{mA}^*$
	$V_{BE(sat)}$		-1.0	V	$I_C = -250\text{mA}, I_B = -25\text{mA}^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$		-0.9	V	$I_C = -250\text{mA}, V_{CE} = -10\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	100 100 85 35	300		$I_C = -1\text{mA}, V_{CE} = -10\text{V}$ $I_C = -100\text{mA}, V_{CE} = -10\text{V}^*$ $I_C = -250\text{mA}, V_{CE} = -10\text{V}^*$ $I_C = -400\text{mA}, V_{CE} = -10\text{V}^*$
Transition Frequency	f_T	150		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		10	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

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TYPICAL CHARACTERISTICS

